

U.S. Application No. 10/014,563

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b6  
b7c*

forming at least one first MEMS component by patterning the single crystal silicon layer; forming at least one second MEMS component by patterning the polysilicon; and depositing at least one layer of polysilicon on the patterned single crystal silicon.

*Sub po 22*

24. (AMENDED) The method of claim 23 wherein the at least one first MEMS component is a mirror retained by the hinge.

*Sub D*

27. (AMENDED) A MEMS formation method including:

providing a SOI wafer including a single crystal silicon layer attached to an insulator layer; forming at least one first MEMS component by patterning the single crystal silicon layer; depositing at least one layer of polysilicon on the patterned single crystal silicon; and wherein forming at least one first MEMS component includes forming a deflecting mirror.

*b7c*

*Sub C3*

30. (AMENDED) A MEMS device comprising:

at least one single crystal silicon component bonded to an insulator that rests on a handle wafer;

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a polysilicon hinge derived from a layer of polysilicon applied over the at least one single crystalline component; and

at least one polysilicon component derived from a layer of polysilicon applied over the at least one single crystalline silicon component.

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31. (AMENDED) The MEMS device of claim 30 wherein the at least one single crystal silicon component comprises a deflecting mirror retained by the hinge.

*in D*

32. (AMENDED) The MEMS device of claim 31 wherein the at least one polysilicon component is attached to and retained by the hinge.

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34. (AMENDED) The MEMS device of claim 30 wherein the at least one polysilicon component is attached to and retained by the hinge.

35. (AMENDED) A MEMS device comprising:

at least one single crystal silicon component bonded to an insulator that rests on a handle wafer; and

at least one polysilicon component derived from a layer of polysilicon applied over the at least one single crystalline silicon component;

a recess in the handle wafer aligned with the at least one single crystal silicon component; and

a semiconductor light emitter mounted in the recess and oriented to emit a light beam at the single crystal silicon component.